

INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION #16790C

Generic Copy

Issue Date: 18-Jan-2012

<u>TITLE:</u> Initial PCN for transfer from the wafer fabs Gunma and Gifu to the On Semiconductor wafer fab ISMF in Malaysia.

PROPOSED FIRST SHIP DATE: starting 31 April 2012 until 30 October 2012 (the actual ship date will be different by each product, please check the responsible Sales person).

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office.

NOTIFICATION TYPE:

Initial Product/Process Change Notification (IPCN)

First change notification sent to customers. IPCNs are issued at least 120 days prior to implementation of the change. An IPCN is advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan.

The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN).

This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change.

DESCRIPTION AND PURPOSE:

This is an Initial Process Change Notification to announce the transfer of products from Sanyo wafer fabrication sites located in Gunma and Gifu, Japan to the ON Semiconductor wafer fabrication site in Seremban, Malaysia. ON Semiconductor's wafer fabrication site in Seremban, Malaysia is certified according to ISO9001:2008, ISO14001:2004,ISO/TS16949:2009 and has been manufacturing similar technology products for over 10 years.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.

Issue Date: 18-Jan-2012 Rev. 06-Jan-2010 Page 1 of 3

ON Semiconductor

INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION #16790C

QUALIFICATION PLAN:

Estimated Date for Qualification Completion: starting February 2012 till September 2012, dependent of the process/product.

Samples should be available after completion of Qualification.

Reliability Test Plan

Test Items	Test Condition	Test ⁻	Time
High Temperature Storage	Tstg max	1000	h
Temperature Humidity Storage	Ta=85°C,RH=85%	1000	h
Steady State Operating Life	Tch,Tjmax	1000	h
High Temperature Revers Bias	Tstg rmax,(VDSSmax,VCESmax,VRmax)	1000	h
Temperature Cycle	Ta=Tstg min to max,30min each	200	Cycle
Pressure Cooker (Autoclave)	Ta=121degC,RH=100%,2.03×10⁵Pa	50	h
Soldering Test	260degC,10s(Soldering bath)	1	time

Notice)

Part Number Identification during transfer

During transfer, we will have mixed products from new fabs and old fabs, so we need to identify which products are from new fabs or old fabs. As a means of the identification, we will add the suffix "X "to the old (existing) product's part number. Your cooperation to this tentative identification method would be appreciated. After the fab transfer is completed, all the product part numbers will turn back to their original part numbers.





Issue Date: 18-Jan-2012 Rev. 06-Jan-2010 Page 2 of 3



INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION #16790C

List of affected parts:

15C01M-TL-E	2SD1628G-TD-H	
SBT150-06J	2SD1685G	
2SA2099	2SD1805F-TL-E	
SBT250-04J	2SD1805G-TL-E	
2SA2125-TD-E	CPH3145-TL-E	
SBT250-06J	CPH6123-TL-E	
2SA2153-TD-E	SB007-03C-TB-E	
SBT350-06J	SB01-15C-TB-E	
2SC5888	SB02-09C-TB-E	
SBT80-04J	SB05-05C-TB-E	
2SC5964-TD-E	SB05W05C-TB-E	
SBT80-06J-YA11	SB07-03C-TB-E	
2SC5994-TD-E	SB10-05P-TD-E	
SBT80-06LS	SBA120-18J	
2SC6082	SBE805-TL-E	
SBT80-10J-CB11	SBE807-TL-E	
2SD1048-7-TB-E	SBR100-10J	
SBT80-10LS	SBR100-16JS	
2SD1618T-TD-E	SBR160-10J	
SBX201C-TB-E	SBR200-16JS	
2SD1060R	SBS811-TL-E	
2SD1620-TDD-E	SBT100-16JS	
2SD1060S	SBT150-04J	
2SD1628G-TD-E		

Issue Date: 18-Jan-2012 Rev. 06-Jan-2010 Page 3 of 3